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(54) Title: MANUFACTURING AND REUSE OF SEMICONDUCTOR SUBSTRATES

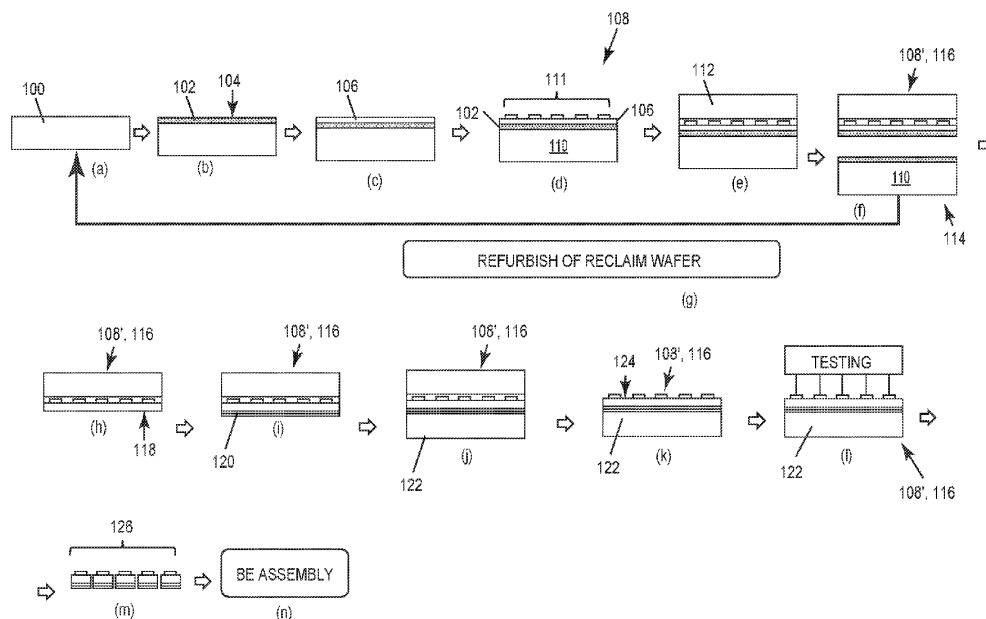


FIG. 1

(57) Abstract: A method of processing a semiconductor wafer includes: forming one or more epitaxial layers over a first main surface of the semiconductor wafer; forming one or more porous layers in the semiconductor wafer or in the one or more epitaxial layers, wherein the semiconductor wafer, the one or more epitaxial layers and the one or more porous layers collectively form a substrate; forming doped regions of a semiconductor device in the one or more epitaxial layers; and after forming the doped regions of the semiconductor device, separating a non-porous part of the semiconductor wafer from a remainder of the substrate along the one or more porous layers.

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